WSB5557Z

Schottky Barrier Diode

Http://www.sh-willsemi.com

Features

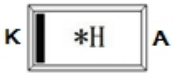
- 100mA Average rectified forward current
- Low forward voltage
- Ultra−low leakage current
- Small package DFN0603-2L

DFN0603-2L(Bottom View)

Circuit

Applications

- Low Current rectification



Marking

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_O	100	mA
Peak forward surge current (8.3ms single sine pluse)	I_{FSM}	2	A
Junction temperature	T_J	150	°C
Operating temperature	Topr	-40 ~ 150	°C
Storage temperature	Tstg	-40 ~ 150	°C

Electronics characteristics (T_A=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Voltage	V_R	I_R=100uA	30			V
Forward Voltage	V_F	I_F=1mA			0.36	V
		I_F=10mA			0.46	V
Reverse current	I_R	V_R=10V			0.3	uA
		V_R=30V			0.5	uA
Junction capacitance	C_J	V_R=5V, F=1MHz		13		pF
Thermal Resistance	$R_{\theta(JA)}$	Junction to Ambient			650	K/W

Order Information

Device	Package	Marking	Shipping
WSB5557Z-2/TR	DFN0603-2L	*H(1)	10000/Reel&Tape

Note 1：*= Month Code(A~Z); H= Device code;

Typical characteristics (Ta=25°C, unless otherwise noted)

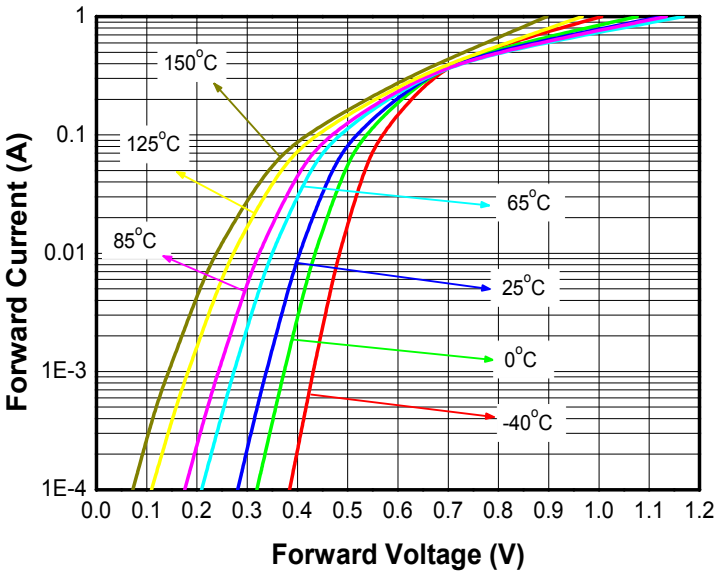


Fig.1 Forward voltage vs. Forward current

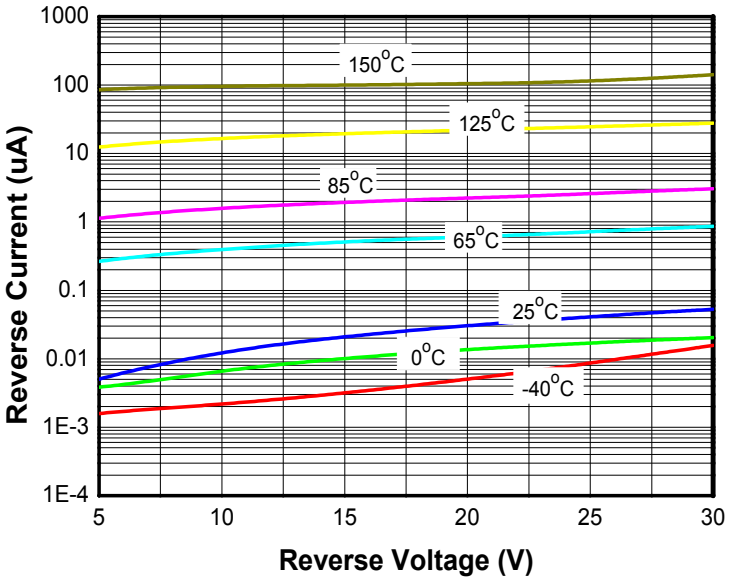


Fig.2 Reverse current vs. Reverse voltage

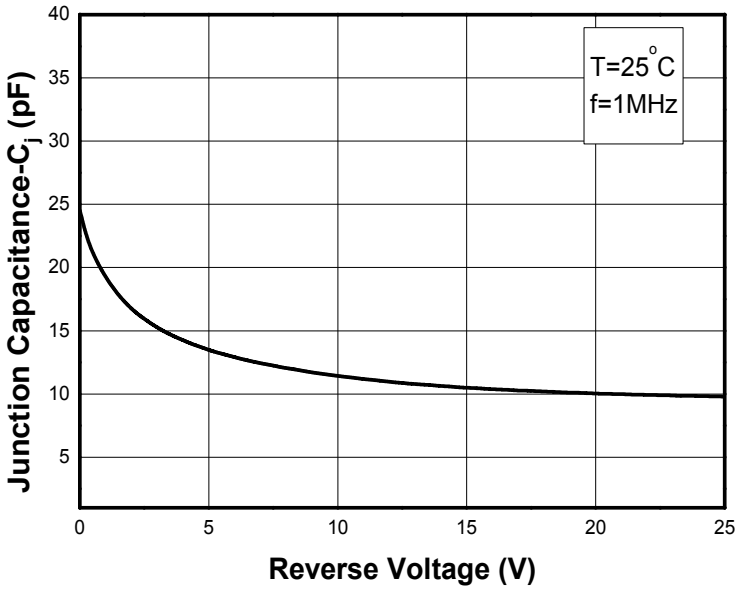
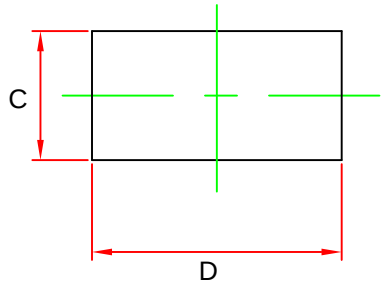
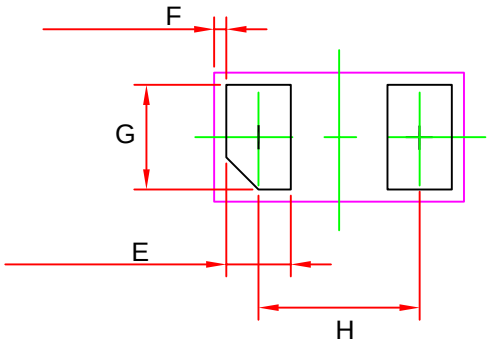


Fig.3 Junction capacitance vs. Reverse voltage

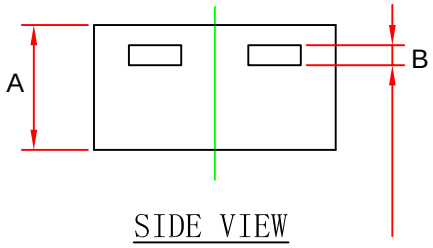
Package outline dimensions



TOP VIEW



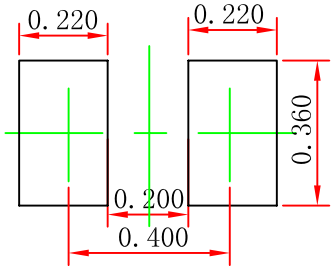
BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.275	0.310	0.340
B		0.050 REF.	
C	0.270	0.320	0.370
D	0.570	0.620	0.670
E	0.125	0.160	0.195
F		0.030 REF.	
G	0.225	0.260	0.295
H	0.365	0.400	0.435

Recommend land pattern (Unit: mm)



Notes:
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.